SN74ACT2226, SN74ACT2228 DUAL 64 × 1, DUAL 256 × 1 CLOCKED FIRST-IN, FIRST-OUT MEMORIES SCAS219C – JUNE 1992 – REVISED OCTOBER 1997

DW PACKAGE (TOP VIEW)

24 1 1RDCLK

23 1 1RDEN

20 2RESET

15 2WRTCLK

14 2AF/AE

13 2HF

22 10R

19 VCC

18 2D

17 21R 16 2WRTEN

21 🛛 1Q

1HF

1AF/AE

1WRTCLK

1WRTEN

1IR 🛛 5

1D 16

2Q 9

20R 110

2RDEN 111

2RDCLK 12

GND 7

1RESET 18

- Dual Independent FIFOs Organized as: 64 Words by 1 Bit Each – SN74ACT2226 256 Words by 1 Bit Each – SN74ACT2228
- Free-Running Read and Write Clocks Can Be Asynchronous or Coincident on Each FIFO
- Input-Ready Flags Synchronized to Write Clocks
- Output-Ready Flags Synchronized to Read Clocks
- Half-Full and Almost-Full/Almost-Empty Flags
- Support Clock Frequencies up to 22 MHz
- Access Times of 20 ns
- Low-Power Advanced CMOS Technology
- Packaged in 24-Pin Small-Outline
 Integrated-Circuit Package

description

The SN74ACT2226 and SN74ACT2228 are dual FIFOs suited for a wide range of serial-data buffering applications, including elastic stores for frequencies up to T2 telecommunication rates. Each FIFO on the chip is arranged as 64×1 (SN74ACT2226) or 256×1 (SN74ACT2228) and has control signals and status flags for independent operation. Output flags for each FIFO include input ready (1IR or 2IR), output ready (1OR or 2OR), half full (1HF or 2HF), and almost full/almost empty (1AF/AE or 2AF/AE).

Serial data is written into a FIFO on the low-to-high transition of the write-clock (1WRTCLK or 2WRTCLK) input when the write-enable (1WRTEN or 2WRTEN) input and input-ready flag (1IR or 2IR) output are both high. Serial data is read from a FIFO on the low-to-high transition of the read-clock (1RDCLK or 2RDCLK) input when the read-enable (1RDEN or 2RDEN) input and output-ready flag (1OR or 2OR) output are both high. The read and write clocks of a FIFO can be asynchronous to one another.

Each input-ready flag (1IR or 2IR) is synchronized by two flip-flop stages to its write clock (1WRTCLK or 2WRTCLK), and each output-ready flag (1OR or 2OR) is synchronized by three flip-flop stages to its read clock (1RDCLK or 2RDCLK). This multistage synchronization ensures reliable flag-output states when data is written and read asynchronously.

A half-full flag (1HF or 2HF) is high when the number of bits stored in its FIFO is greater than or equal to half the depth of the FIFO. An almost-full/almost-empty flag (1AF/AE or 2AF/AE) is high when eight or fewer bits are stored in its FIFO and when eight or fewer empty locations are left in the FIFO. A bit present on the data output is not stored in the FIFO.

The SN74ACT2226 and SN74ACT2228 are characterized for operation from -40°C to 85°C.

For more information on this device family, see the application report *FIFOs With a Word Width of One Bit* (literature number SCAA006).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

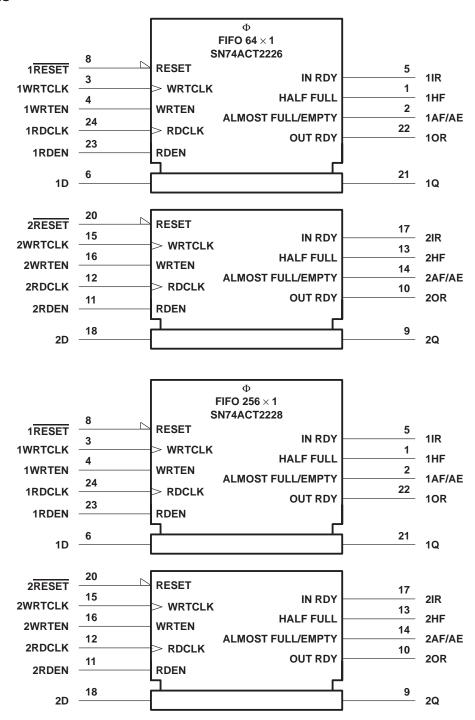
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SN74ACT2226, SN74ACT2228 DUAL 64 × 1, DUAL 256 × 1 CLOCKED FIRST-IN, FIRST-OUT MEMORIES SCAS219C – JUNE 1992 – REVISED OCTOBER 1997

logic symbols[†]

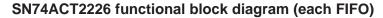


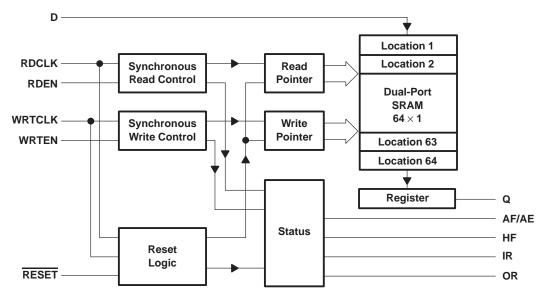
[†] These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



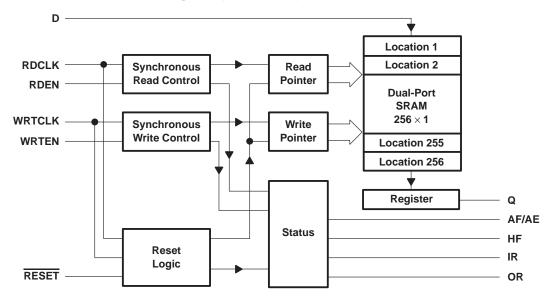
SN74ACT2226, SN74ACT2228 DUAL 64 \times 1, DUAL 256 \times 1 **CLOCKED FIRST-IN, FIRST-OUT MEMORIES**

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SN74ACT2228 functional block diagram (each FIFO)





SN74ACT2226, SN74ACT2228 DUAL 64 × 1, DUAL 256 × 1 CLOCKED FIRST-IN, FIRST-OUT MEMORIES SCAS219C - JUNE 1992 - REVISED OCTOBER 1997

Terminal Functions

TERMIN	AL		DECODIDECON
NAME	NO.	1/0	DESCRIPTION
1AF/AE 2AF/AE	2 14	0	Almost-full/almost-empty flag. AF/AE is high when the memory is eight locations or less from a full or empty state. AF/AE is set high after reset.
1D 2D	6 18	I	Data input
GND	7		Ground
1HF 2HF	1 13	0	Half-full flag. HF is high when the number of bits stored in memory is greater than or equal to half the FIFO depth. HF is set low after reset.
1IR 2IR	5 17	0	Input-ready flag. IR is synchronized to the low-to-high transition of WRTCLK. When IR is low, the FIFO is full and writes are disabled. IR is set low during reset and is set high on the second low-to-high transition of WRTCLK after reset.
10R 22 20R 10 0			Output-ready flag. OR is synchronized to the low-to-high transition of RDCLK. When OR is low, the FIFO is empty and reads are disabled. Ready data is present on the data output when OR is high. OR is set low during reset and set high on the third low-to-high transition of RDCLK after the first word is loaded to empty memory.
1Q 2Q	21 9	0	Data outputs. After the first valid write to empty memory, the first bit is output on the third rising edge of RDCLK. OR for the FIFO is asserted high to indicate ready data.
1RDCLK 2RDCLK	24 12	I	Read clock. RDCLK is a continuous clock and can be independent of any other clock on the device. A low-to-high transition of RDCLK reads data from memory when the FIFO RDEN and OR are high. OR is synchronous with the low-to-high transition of RDCLK.
1RDEN 2RDEN	23 11	I	Read enable. When the RDEN and OR of a FIFO are high, data is read from the FIFO on the low-to-high transition of RDCLK.
1 <u>RESET</u> 2RESET	8 20	I	Reset. To reset the FIFO, four low-to-high transitions of RDCLK and four low-to-high transitions of WRTCLK must occur while RESET is low. This sets HF, IR, and OR low and AF/AE high. Before it is used, a FIFO must be reset after power up.
VCC	19		Supply voltage
1WRTCLK 2WRTCLK	3 15	I	Write clock. WRTCLK is a continuous clock and can be independent of any other clock on the device. A low-to-high transition of WRTCLK writes data to memory when WRTEN and IR are high. IR is synchronous with the low-to-high transition of WRTCLK.
1WRTEN 2WRTEN	4 16	I	Write enable. When WRTEN and IR are high, data is written to the FIFO on a low-to-high transition of WRTCLK.



SN74ACT2226, SN74ACT2228 DUAL 64 \times 1, DUAL 256 \times 1 CLOCKED FIRST-IN, FIRST-OUT MEMORIES SCAS219C – JUNE 1992 – REVISED OCTOBER 1997

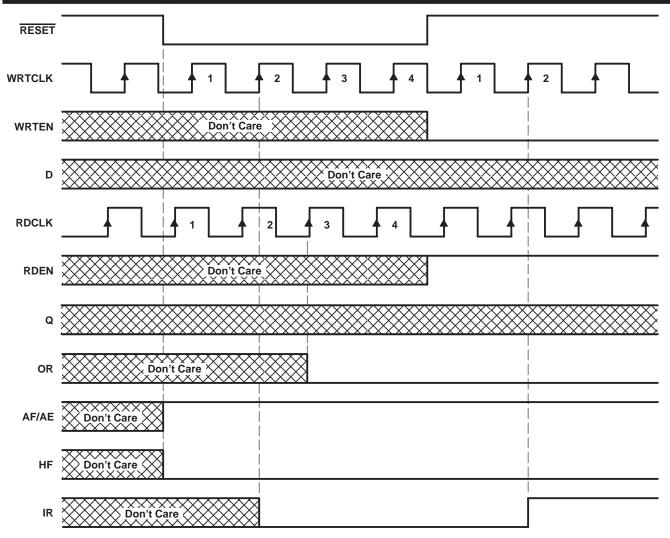
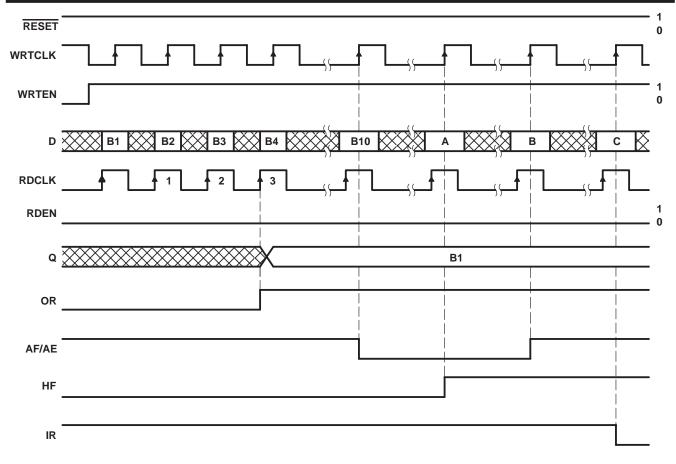


Figure 1. FIFO Reset



SN74ACT2226, SN74ACT2228 DUAL 64 \times 1, DUAL 256 \times 1 CLOCKED FIRST-IN, FIRST-OUT MEMORIES SCAS219C – JUNE 1992 – REVISED OCTOBER 1997



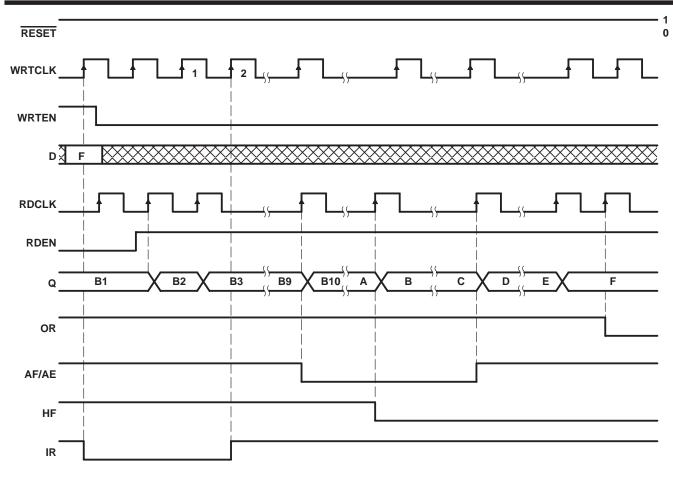
DATA BIT NUMBER BASED ON FIFO DEPTH

DEVICE	[DATA BI	Г
DEVICE	А	В	С
SN74ACT2226	B33	B57	B65
SN74ACT2228	B129	B249	B257

Figure 2. FIFO Write



SN74ACT2226, SN74ACT2228 DUAL 64 \times 1, DUAL 256 \times 1 CLOCKED FIRST-IN, FIRST-OUT MEMORIES SCAS219C – JUNE 1992 – REVISED OCTOBER 1997



DATA BIT NUMBER BASED ON FIFO DEPTH

DEVICE			DATA	A BIT		
DEVICE	Α	В	С	D	Е	F
SN74ACT2226	B33	B34	B56	B57	B64	B65
SN74ACT2228	B129	B130	B248	B249	B256	B257

Figure 3. FIFO Read



SN74ACT2226, SN74ACT2228 DUAL 64 \times 1, DUAL 256 \times 1 **CLOCKED FIRST-IN, FIRST-OUT MEMORIES**

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V_{CC} Input voltage range, V_I (see Note 1) Output voltage range, V_O (see Note 1) Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) Continuous output current, I_O ($V_O = 0$ to V_{CC}) Continuous current through V_{CC} or GND Package thermal impedance, θ_{JA} (see Note 2) Storage temperature range T	$\begin{array}{c} -0.5 \mbox{ V to } V_{CC} + 0.5 \mbox{ V} \\ -0.5 \mbox{ V to } V_{CC} + 0.5 \mbox{ V} \\ \pm 20 \mbox{ mA} \\ \pm 50 \mbox{ mA} \\ \pm 50 \mbox{ mA} \\ \pm 200 \mbox{ mA} \\ \end{array}$
Storage temperature range, T _{stg}	

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded provided that the input and output current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

		MIN	MAX	UNIT
Vcc	4.5	5.5	V	
VIH	2		V	
VIL	Low-level input voltage		0.8	V
ЮН	High-level output current Q outputs, flags		-8	mA
1	Low-level output current Q outputs		16	
^I OL	Flags		8	mA
ТА	Operating free-air temperature	-40	85	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER		TEST CONDITIONS	MIN	TYP [‡]	MAX	UNIT
∨он		V _{CC} = 4.5 V,	$I_{OH} = -8 \text{ mA}$	2.4			V
VOL	Flags	V _{CC} = 4.5 V,	I _{OL} = 8 mA			0.5	V
VOL	Q outputs	V _{CC} = 4.5 V,	I _{OL} = 16 mA			0.5	v
Ц		V _{CC} = 5.5 V,	VI = VCC or 0			±5	μA
IOZ		V _{CC} = 5.5 V,	VO = ACC or 0			±5	μΑ
ICC		$V_{I} = V_{CC} - 0.2 V_{C}$	or 0			400	μA
∆ICC§		V _{CC} = 5.5 V,	One input at 3.4 V, Other inputs at V_{CC} or GND			1	mA
Ci		$V_{I} = 0,$	f = 1 MHz		4		pF
Co		$V_{O} = 0,$	f = 1 MHz		8		pF

[‡] All typical values are at V_{CC} = 5 V, T_A = 25° C.

 $^{\$}$ This is the supply current when each input is at one of the specified TTL voltage levels rather than 0 V or V_{CC}.



SN74ACT2226, SN74ACT2228 DUAL 64 × 1, DUAL 256 × 1 CLOCKED FIRST-IN, FIRST-OUT MEMORIES SCAS219C – JUNE 1992 – REVISED OCTOBER 1997

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figures 1 through 3)

			MIN	MAX	UNIT
fclock	Clock frequency			22	MHz
	Pulse duration	1WRTCLK, 2WRTCLK high or low	15		20
tw	Pulse duration	1RDCLK, 2RDCLK high or low	15		ns
		1D before 1WRTCLK [↑] and 2D before 2WRTCLK [↑]	6		
		1WRTEN before 1WRTCLK [↑] and 2WRTEN before 2WRTCLK [↑]	6		
t _{su} Setup time	1RDEN before 1RDCLK [↑] and 2RDEN before 2RDCLK [↑]	6		ns	
		1RESET low before 1WRTCLK↑ and 2RESET low before 2WRTCLK↑†	6		
		1RESET low before 1RDCLK [↑] and 2RESET low before 2RDCLK ^{↑†}	6		
		1D after 1WRTCLK [↑] and 2D after 2WRTCLK [↑]	0		
		1WRTEN after 1WRTCLK [↑] and 2WRTEN after 2WRTCLK [↑]	0		
t _h Hold time	1RDEN after 1RDCLK [↑] and 2RDEN after 2RDCLK [↑]	0		ns	
		1RESET low after 1WRTCLK↑ and 2RESET low after 2WRTCLK↑†	6		
		1RESET low after 1RDCLK [↑] and 2RESET low after 2RDCLK ^{↑†}	6		

[†]Requirement to count the clock edge as one of at least four needed to reset a FIFO

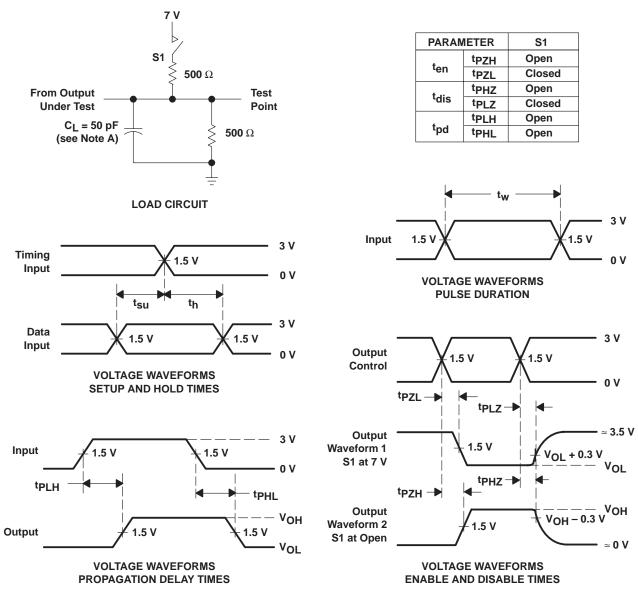
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN	МАХ	UNIT
fmax	1WRTCLK, 2WRTCLK, or 1RDCLK, 2RDCLK		22		MHz
	1RDCLK↑, 2RDCLK↑	1Q, 2Q	2	20	
	1WRTCLK [↑] , 2WRTCLK [↑]	1IR, 2IR	1	20	
^t pd	1RDCLK [↑] , 2RDCLK [↑]	10R, 20R	1	20	ns
	1WRTCLK [↑] , 2WRTCLK [↑]		3	20	
	1RDCLK [↑] , 2RDCLK [↑]	1AF/AE, 2AF/AE	3	20	
^t PLH	1WRTCLK [↑] , 2WRTCLK [↑]		2	20	
^t PHL	1RDCLK↑, 2RDCLK↑	1HF, 2HF	3	20	ns
^t PLH	1RESET, 2RESET low	1AF/AE, 2AF/AE	1	20	00
^t PHL	INESET, ZRESET IOW	1HF, 2HF	1	20	ns



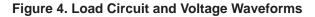
SN74ACT2226, SN74ACT2228 DUAL 64 \times 1, DUAL 256 \times 1 **CLOCKED FIRST-IN, FIRST-OUT MEMORIES**

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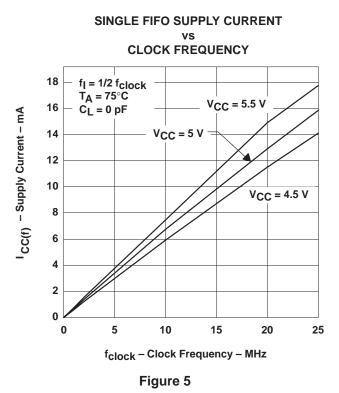




NOTE A: CL includes probe and jig capacitance.







TYPICAL CHARACTERISTICS

calculating power dissipation

Data for Figure 5 is taken with one FIFO active and one FIFO idle on the device. The active FIFO has both writes and reads enabled with its read clock (RDCLK) and write clock (WRTCLK) operating at the rate specified by f_{clock} . The data input rate and data output rate are half the f_{clock} rate, and the data output is disconnected. A close approximation of the total device power can be found by using Figure 5, determining the capacitive load on the data output and determining the number of SN74ACT2226/2228 inputs driven by TTL high levels.

With $I_{CC(f)}$ taken from Figure 5, the maximum power dissipation (P_T) of one FIFO on the SN74ACT2226 or SN74ACT2228 can be calculated by:

$$\mathsf{P}_{\mathsf{T}} = \mathsf{V}_{\mathsf{C}\mathsf{C}} \times [\mathsf{I}_{\mathsf{C}\mathsf{C}(\mathsf{f})} + (\mathsf{N} \times \Delta \mathsf{I}_{\mathsf{C}\mathsf{C}} \times \mathsf{d}\mathsf{c})] + (\mathsf{C}_{\mathsf{L}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}^2 \times \mathsf{f}_{\mathsf{o}})$$

where:

- N = number of inputs driven by TTL levels
- ΔI_{CC} = increase in power-supply current for each input at a TTL high level
- dc = duty cycle of inputs at a TTL high level of 3.4 V
- CL = output capacitive load
- f_0 = switching frequency of an output



SN74ACT2226, SN74ACT2228 DUAL 64 \times 1, DUAL 256 \times 1 CLOCKED FIRST-IN, FIRST-OUT MEMORIES

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APPLICATION INFORMATION

An example of concentrating two independent serial-data signals into a single composite data signal with the use of an SN74ACT2226 or SN74ACT2228 device is shown in Figure 6. The input data to the FIFOs share the same average (mean) frequency and the mean frequency of the SYS_CLOCK is greater than or equal to the sum of the individual mean input rates. A single-bit FIFO is needed for each additional input data signal that is time-division multiplexed into the composite signal.

The FIFO memories provide a buffer to absorb clock jitter generated by the transmission systems of incoming signals and synchronize the phase-independent inputs to one another. FIFO half-full (HF) flags are used to signal the multiplexer to start fetching data from the buffers. The state of the flags also can be used to indicate when a FIFO read should be suppressed to regulate the output flow (pulse-stuffing control). The FIFO almost-full/almost-empty (AF/AE) flags can be used in place of the half-full flags to reduce transmission delay.

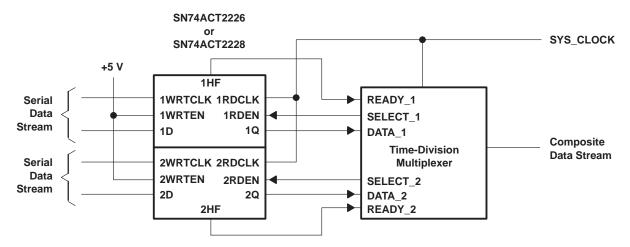


Figure 6. Time-Division Multiplexing Using the SN74ACT2226 or SN74ACT2228



PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN74ACT2226DW	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74ACT2226DWR	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74ACT2228DW	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74ACT2228DWR	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

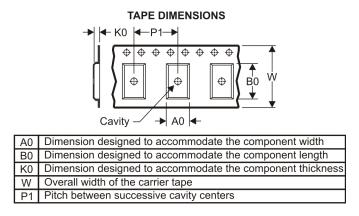
⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

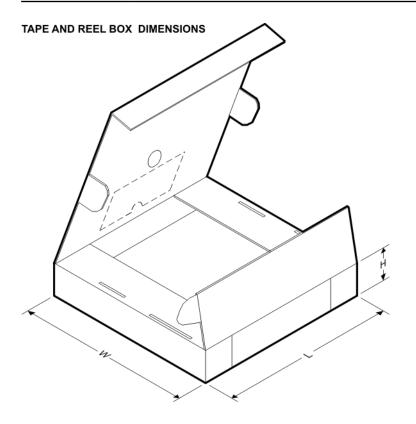


*	All dimensions are nominal												
	Device	-	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
	SN74ACT2226DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
	SN74ACT2228DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1



PACKAGE MATERIALS INFORMATION

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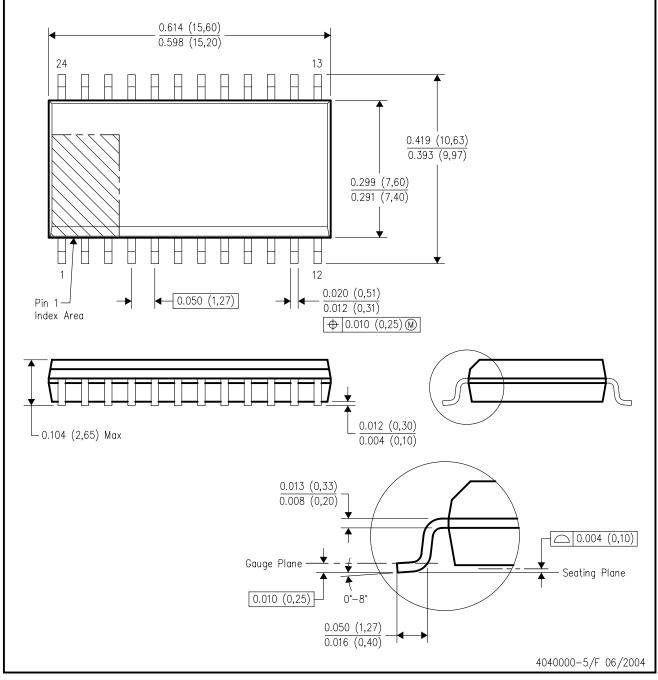


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74ACT2226DWR	SOIC	DW	24	2000	346.0	346.0	41.0
SN74ACT2228DWR	SOIC	DW	24	2000	346.0	346.0	41.0

DW (R-PDSO-G24)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-013 variation AD.





PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	(-)		-		•	(-)	(6)	(-)		(12)	
SN74ACT2226DW	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ACT2226	Samples
SN74ACT2228DW	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ACT2228	Samples
SN74ACT2228DWR	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ACT2228	Samples

⁽¹⁾ The marketing status values are defined as follows:

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PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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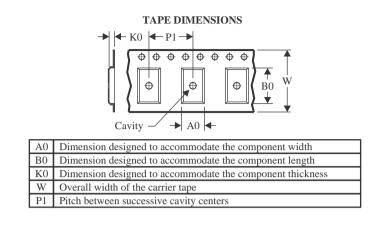
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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	•	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	` '	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74ACT2228DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1



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PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74ACT2228DWR	SOIC	DW	24	2000	350.0	350.0	43.0

TEXAS INSTRUMENTS

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TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
SN74ACT2226DW	DW	SOIC	24	25	506.98	12.7	4826	6.6
SN74ACT2228DW	DW	SOIC	24	25	506.98	12.7	4826	6.6

DW (R-PDSO-G24)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-013 variation AD.



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